

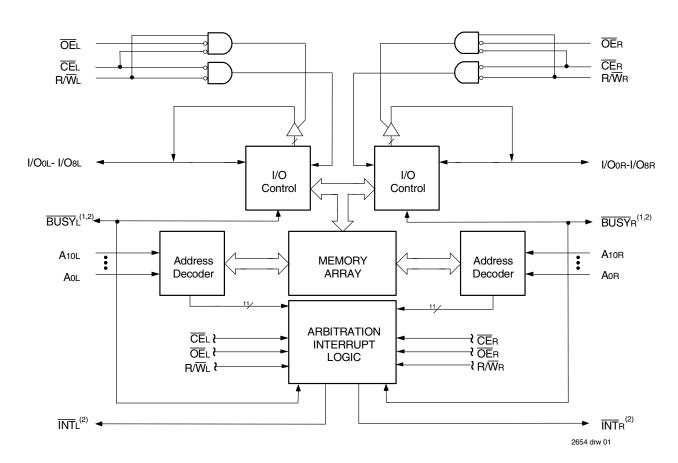
HIGH-SPEED 2K x 9 DUAL-PORT STATIC RAM WITH BUSY & INTERRUPT

70121L 70125L

Features

- * High-speed access
 - Commercial: 25ns (max.)
- Low-power operation
 - IDT70121/70125L
 Active: 675mW (typ.)
 Standby: 1mW (typ.)
- MASTER IDT70121 easily expands data bus width to 18 bits or more using SLAVE IDT70125 chip
- Fully asychronous operation from either port
- On-chip port arbitration logic (IDT70121 only)
- BUSY output flag on Master; BUSY input on Slave
- INT flag for port-to-port communication
- Battery backup operation—2V data retention
- * TTL-compatible, signal 5V (±10%) power supply
- Available in 52-pin PLCC
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

- 70121 (MASTER): BUSY is non-tri-stated push-pull output. 70125 (SLAVE): BUSY is input.
- 2. INT is non-tri-stated push-pull output.

SEPTEMBER 2019



Commercial Temperature Range

Description

The IDT70121/IDT70125 are high-speed 2K x 9 Dual-Port Static RAMs. The IDT70121 is designed to be used as a stand-alone 9-bit Dual-Port RAM to gether with the IDT70125 "SLAVE" Dual-Port in 18-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 18-bit-or-wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power-down

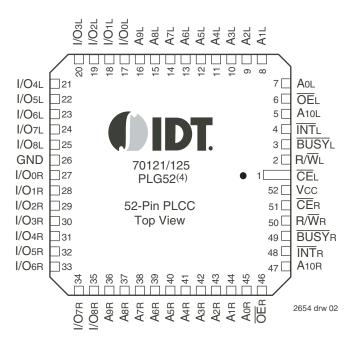
feature, controlled by $\overline{\text{CE}}$, permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT70121/IDT70125 utilizes a 9-bit wide data path to allow for Data/Control and parity bits at the user's option. This feature is especially useful in data communications applications where it is necessary to use a parity bit for transmission/reception error checking.

Fabricated using CMOS high-performance technology, these devices typically operate on only 675mW of power. Low-power (L) versions offer battery backup data retention capability with each port typically consuming 200µW from a 2V battery.

The IDT70121/IDT70125 devices are packaged in a 52-pin PLCC.

Pin Configurations (1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply
- 3. Package body is approximately .75 in x .75 in x .17 in.
- 4. This package code is used to reference the package diagram.



Commercial Temperature Range

2654 tbl 03

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	۰C
Tstg	Storage Temperature	-65 to +150	°C
ЮИТ	DC Output Current	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.8	V

NOTES:

- 1. $VIL \ge -1.5V$ for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

Capacitance (TA = +25°C, f = 1.0MHz)

Syn	nbol	Parameter	Conditions ⁽¹⁾	Max.	Unit
С	IN	Input Capacitance	VIN = 3dV	9	pF
Co	DUT	Output Capacitance	Vout = 3dV	10	pF

NOTE:

 This parameter is determined by device characterization but is not production tested

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($Vcc = 5.0V \pm 10\%$)

		1 3 3 5 1		,			
			70121S 70125S			21L 25L	
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $VIN = 0V$ to Vcc	_	10	_	5	μΑ
luo	Output Leakage Current	$Vcc = 5.5V$, $\overline{CE} = ViH$, $Vout = 0V$ to Vcc	_	10	_	5	μΑ
Vol	Output Low Voltage	IoL = +4mA	_	0.4	ı	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	V

2654 tbl 02

NOTE:

1. At $Vcc \le 2.0V$ leakages are undefined.

2654 tbl 05

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(1,4)}$ (Vcc = 5V \pm 10%)

					7012	1X25 5X25 I Only			
Symbol	Parameter	Test Condition	Versio	on	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CE = V _L , Outputs Disabled	COM'L	S L	135 135	260 220	135 135	250 210	mA
		$f = fMAX^{(2)}$	IND	S L			135 135	275 250	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	\overline{CE} 'A" = \overline{CE} 'B" = VIH $f = fMAX^{(2)}$	COM'L	S L	30 30	65 45	30 30	65 45	mA
		IND	IND	S L		_	30 30	80 65	
ISB2	Standby Current (One Port - TTL Level Inputs)	CE'A" = VIL and CE'B" = VIH ⁽⁵⁾ Active Port Outputs Disabled, f=ftMAX ⁽²⁾	COM'L	S L	80 80	175 145	80 80	165 135	mA
		I=IVIAX **	IND	S L	11	1 1	80 80	190 165	
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	\overline{CE} 'A" and \overline{CE} 'B" \geq VCC - 0.2V VIN \geq VCC - 0.2V or VIN \leq 0.2V, f = 0 ⁽³⁾	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	mA
		VIIV <u><</u> 0.2V, 1 = 0 [∞] /	IND	S L	1 1		1.0 0.2	15 5	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VCC - 0.2V^{(5)}$	COM'L	S L	70 70	170 140	70 70	160 130	mA
		V IN $\geq \overline{V}$ CC - 0.2V or V IN \leq 0.2V Active Port Outputs Disabled, $f = f$ MAX $^{(2)}$	IND	S L			70 70	185 160	

2654 tbl 06a

2654 tbl 06b

					7012 7012 Com'l		
Symbol	Parameter	Test Condition	Versio	n	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CE = VIL, Outputs Disabled	COM'L	S L	135 135	240 200	mA
		$f = fMAX^{(2)}$	IND	S L			
ISB1	Standby Current (Both Ports - TTL Level Inputs)	\overline{CE} "A" = \overline{CE} "B" = VIH	COM'L	S L	30 30	65 45	mA
		$f = fMAX^{(2)}$	IND	S L			
ISB2	Standby Current (One Port - TTL Level Inputs)	CE"A" = VIL and CE"B" = VIH ⁽⁵⁾ Active Port Outputs Disabled, f=fMAX ⁽²⁾	COM'L	S L	80 80	155 125	mA
		I=IMAX**/	IND	S L			
ISB3	Full Standby Current (Both Ports - CMOS Level	$\overline{\text{CE}}$ "A" and $\overline{\text{CE}}$ "B" \geq VCC - 0.2V VIN \geq VCC - 0.2V or	COM'L	S L	1.0 0.2	15 5	mA
	Inputs)	$VIN \le 0.2V, f = 0^{(3)}$	IND	S L			
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	<u>CE</u> "A" ≤ 0.2V and <u>CE</u> "B" ≥ VCC - 0.2V ⁽⁵⁾	COM'L	S L	70 70	150 120	mA
	(energy conducting and angular	$VIN \ge \overline{V}CC - 0.2V$ or $VIN \le 0.2V$ Active Port Outputs Disabled, $f = fMAX^{(2)}$	IND	S L			

NOTES:

- 1. 'X' in part numbers indicates power rating (S or L).
- 2. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC TEST CONDITIONS" of input levels of GND to 3V.
- 3. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 4. Vcc=5V, Ta=+25°C for Typ, and is not production tested.
- 5. Port "A" may be either left or right port. Port "B" is opposite from port "A".

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Commercial Temperature Range

Data Retention Characteristics (L Version Only)

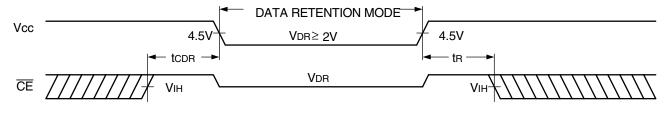
Symbol	Parameter	Test Condition		Min.	Typ. ⁽¹⁾	Max.	Unit
VDR	Vcc for Data Retention			2.0	_		V
ICCDR	Data Retention Current	$Vcc = 2V$, $\overline{CE} \ge Vcc - 0.2V$	IND.	_	100	4000	μΑ
tcdr ⁽³⁾	Chip Deselect to Data Retention Time	V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2	COM'L.	_	100	1500	
tr ⁽³⁾	Operation Recovery Time			trc ⁽²⁾	_	_	٧

2654 tbl 07

NOTES:

- 1. Vcc = 2V, TA = +25°C, and are not production tested.
- 2. trc = Read Cycle Time.
- 3. This parameter is guaranteed but is not production tested.

Data Retention Waveform



2654 drw 03

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

2654 tbl 08

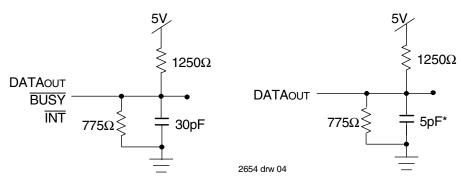


Figure 1. AC Output Test Load

Figure 2. Output Test Load (For tLz, tHz, twz, tow) *Including scope and jig.



Commercial Temperature Range

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾

		70121X25 70125X25 Com'l Only		70121X35 70125X35 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
trc	Read Cycle Time	25	_	35	_	ns
taa	Address Access Time	_	25	_	35	ns
tace	Chip Enable Access Time		25		35	ns
taoe	Output Enable Access Time	_	12	_	25	ns
tон	Output Hold from Address Change	0	_	0	_	ns
tLZ	Output Low-Z Time ^(1,2)	0	_	0	_	ns
tHZ	Output High-Z Time ^(1,2)	_	10	_	15	ns
tpu	Chip Enable to Power Up Time (2)	0	_	0	_	ns
tpD	Chip Disable to Power Down Time ⁽²⁾		50	_	50	ns

2654 tbl 09a

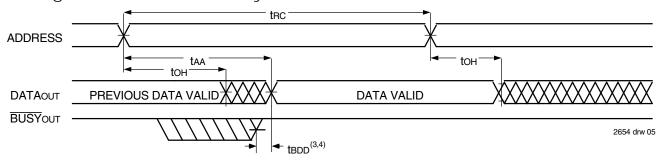
		7012	70121X55 70125X55 Com'l Only	
Symbol	Parameter	Min.	Max.	Unit
READ CYCLE				
trc	Read Cycle Time	55	_	ns
taa	Address Access Time	_	55	ns
tace	Chip Enable Access Time	_	55	ns
taoe	Output Enable Access Time	_	35	ns
toн	Output Hold from Address Change	0	_	ns
tLZ	Output Low-Z Time ^(1,2)	0	_	ns
tHZ	Output High-Z Time ^(1,2)	_	30	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0	_	ns
tpD	Chip Disable to Power Down Time ⁽²⁾		50	ns

2654 tbl 09b

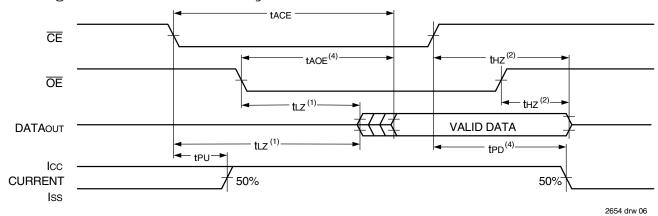
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. This parameter guaranteed by device characterization, but is not production tested.
- 3. 'X' in part numbers indicates power rating (S or L).



Timing Waveform of Read Cycle No. 1, Either Side(1,2,4)



Timing Waveform of Read Cycle No. 2, Either Side⁽⁵⁾



- 1. Timing depends on which signal is asserted last, \overline{OE} or \overline{CE} .
- 2. Timing depends on which signal is de-asserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. tBDD delay is required only in a case where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 4. Start of valid data depends on which timing becomes effective last, tAOE, tACE, tAA, or tBDD.
- 5. $R\overline{W} = V_{H}$, $\overline{CE} = V_{IL}$, and $\overline{OE} = V_{IL}$, and the address is valid prior to other coincidental with \overline{CE} transition LOW.



Commercial Temperature Range

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾

		70121X25 70125X25 Com'l Only		70121X35 70125X35 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE						
twc	Write Cycle Time (4)	25	_	35	_	ns
tew	Chip Enable to End-of-Write	20		30		ns
taw	Address Valid to End-of-Write	20	1	30		ns
tas	Address Set-up Time	0	I	0	-	ns
twp	Write Pulse Width ⁽⁶⁾	20		30		ns
twr	Write Recovery Time	0	1	0		ns
tow	Data Valid to End-of-Write	12	I	20	I	ns
tHZ	Output High-Z Time ^(1,2,3)		10	I	15	ns
tон	Data Hold Time ⁽⁵⁾	0		0	_	ns
twz	Write Enable to Output in High- $\mathbb{Z}^{(1,3)}$		10	-	15	ns
tow	Output Active from End-of-Write (1,2,3,5)	0	_	0	_	ns

2654 tbl 10a

		7012 7012 Com'l			
Symbol	Parameter	Min.	Unit		
WRITE CYCLE					
twc	Write Cycle Time ⁽⁴⁾	55	_	ns	
tew	Chip Enable to End-of-Write	40	_	ns	
taw	Address Valid to End-of-Write	40		ns	
tas	Address Set-up Time	0		ns	
twp	Write Pulse Width ⁽⁶⁾	40		ns	
twr	Write Recovery Time	0		ns	
tow	Data Valid to End-of-Write	20		ns	
tHZ	Output High-Z Time ^(1,2,3)		30	ns	
tон	Data Hold Time ⁽⁵⁾	0	I	ns	
twz	Write Enable to Output in High-Z ^(1,3)	_	30	ns	
tow	Output Active from End-of-Write ^(1,2,3,5)	0	_	ns	

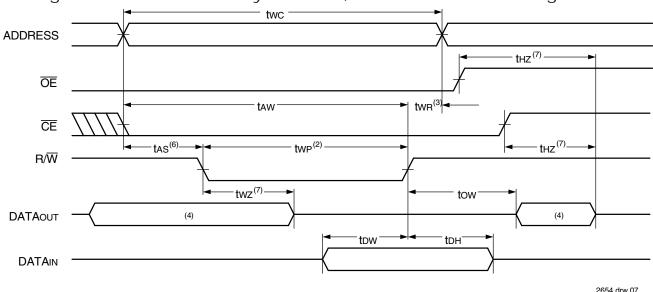
_ _ 2654 tbl 10b

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter guaranteed by device characterization, but is not production tested.
- 3. For MASTER/SLAVE combination, two = tbaa + twp, since R/W = VIL must occur after tbaa.
- 4. 'X' in part numbers indicates power rating (S or L).
- 5. The specified toH must be met by the device supplying write date to the RAM under all operating conditions. Although toH and tow values will vary over voltage and temperature. The actual toH will always be smaller than the actual tow.
- 6. If \overline{OE} is LOW during a R/ \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R/ \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

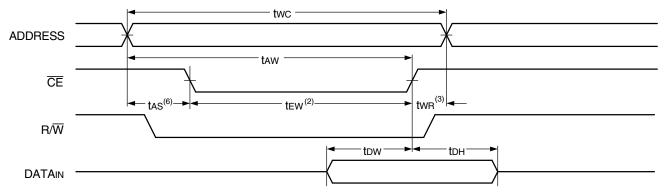
8



Timing Waveform of Write Cycle No. 1, R/W Controlled Timing (1,5,8)



Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)



2654 drw 08

- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} = V_{IL} and a R/ \overline{W} = V_{IL}
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or R/\overline{W} going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during a \overline{RW} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a \overline{RW} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{\rm (6)}$

					70121X35 70125X35 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	(For MASTER IDT70121)					
tbaa	BUSY Access Time from Address		20		20	ns
tBDA	BUSY Disable Time from Address	_	20	_	20	ns
t BAC	BUSY Access Time from Chip Enable		20	_	20	ns
tBDC	BUSY Disable Time from Chip Enable		20	_	20	ns
twdd	Write Pulse to Data Delay ⁽¹⁾		50		60	
todo	Write Data Valid to Read Data Delay ⁽¹⁾		35		45	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		30	_	30	ns
twн	Write Hold After BUSY ⁽⁵⁾	15	_	20		ns
BUSY INPUT	TIMING (For SLAVE IDT70125)					
twB	Write to BUSY Input ⁽⁴⁾	0	_	0		ns
twн	Write Hold After BUSY ⁽⁵⁾	15	_	20		ns
twdd	Write Pulse to Data Delay ⁽¹⁾	_	50	_	60	ns
todo	Write Data Valid to Read Data Delay ⁽¹⁾		35		45	ns

2654 tbl 11a

		7012 7012 Com'		
Symbol	Parameter	Min.	Max.	Unit
BUSY TIMING (For MASTER IDT 70121)				
tbaa	BUSY Access Time from Address	_	30	ns
tbda	BUSY Disable Time from Address	_	30	ns
tBAC	BUSY Access Time from Chip Enable	_	30	ns
tBDC	BUSY Disable Time from Chip Enable	_	30	ns
twdd	Write Pulse to Data Delay ⁽¹⁾		80	
todo	Write Data Valid to Read Data Delay ⁽¹⁾		65	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		ns
tbdd	BUSY Disable to Valid Data ⁽³⁾		45	ns
twn	Write Hold After BUSY ⁽⁵⁾	20		ns
BUSY INPUT	TIMING (For SLAVE IDT 70125)			
twB	Write to BUSY Input ⁽⁴⁾	0		ns
twн	Write Hold After BUSY ⁽⁵⁾	20		ns
twdd	Write Pulse to Data Delay ⁽¹⁾	_	80	ns
todo	Write Data Valid to Read Data Delay ⁽¹⁾	_	65	ns

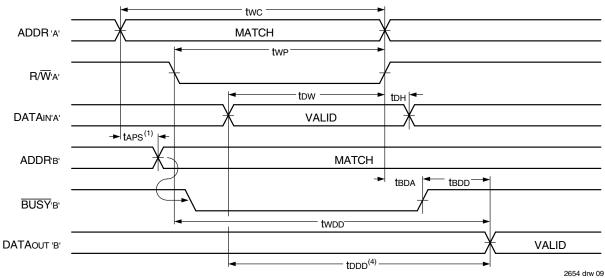
NOTES:

2654 tbl 11b

- 1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY.
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 4. To ensure that a write cycle is inhibited on port 'B' during contention on port 'A'...
- 5. To ensure that a write cycle is completed on port 'B' after contention on port 'A'.
- 6. 'X' in part numbers indicates power rating (S or L).



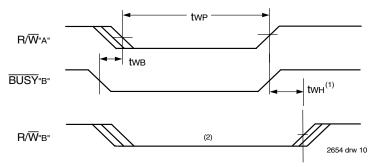
Timing Waveform of Write with Port-to-Port Read and **BUSY**(1,2,3)



NOTES:

- To ensure that the earlier of the two ports wins. taps is ignored for Slave (IDT70125).
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

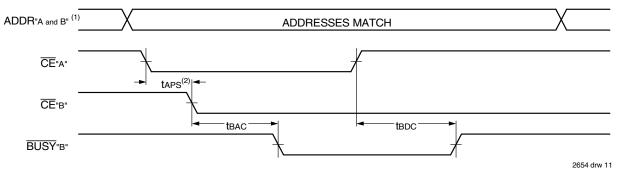
Timing Waveform of Write with **BUSY**(3)



NOTES:

- 1. twh must be met for both BUSY input (slave) and output (master).
- 2. BUSY is asserted on port 'B' blocking R/W'B', until BUSY'B' goes HIGH.
- 3. All timing is the same for left and right ports. Port"A" may be either left or right port. Port "B" is the opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾

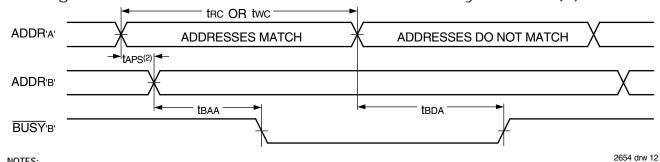


- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (70121 only).



Commercial Temperature Range

Timing Waveform of **BUSY** Arbitration Controlled by Address(1)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (70121 only).

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

		70121X25 70121X35 70125X25 70125X35 Com'l Only Com'l & Ind		5X35 m'l		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
INTERRUPT T	IMING		-		-	
tas	Address Set-up Time	0	_	0	_	ns
twr	Write Recovery Time	0		0	_	ns
tins	Interrupt Set Time		25	_	35	ns
tinr	Interrupt Reset Time		25	_	35	ns

2654 tbl 12a

		7012 7012 Com'l		
Symbol	Parameter	Min.	Max.	Unit
INTERRUPT 1	IMING			
tas	Address Set-up Time	0		ns
twr	Write Recovery Time	0		ns
tins	Interrupt Set Time	_	45	ns
tinr	Interrupt Reset Time	_	45	ns

2654 tbl 12b

NOTES

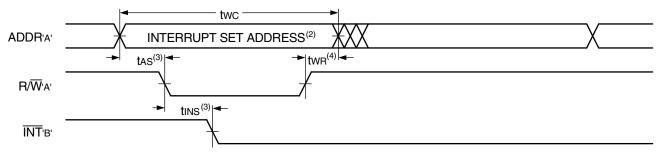
1. 'X' in part numbers indicates power rating (S or L).



Commercial Temperature Range

2654 drw 13

Timing Waveform of Interrupt Mode⁽¹⁾



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table.
- 3. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal $(\overline{CE} \text{ or } R/\overline{W})$ is de-asserted first.

Truth Tables

Truth Table I. Non-Contention Read/Write Control⁽⁴⁾

	Left or Right Port ⁽¹⁾			
R/W	CE	Œ	D ₀₋₈	Function
Х	Н	Х	Z	Port Disable and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	CER = CEL = H, Power-DownMode, ISB1 or ISB3
L	L	Х	DATAIN	Data on Port Written Into Memory ⁽²⁾
Н	L	L	DATAout	Data in Memory Output on Port ⁽³⁾
Н	L	Н	Z	High-Impedance Outputs

NOTES: 2654 tbl 13

- 1. $A0L A10L \neq A0R A10R$.
- 2. If $\overline{\text{BUSY}} = L$, data is not written.
- 3. If $\overline{\text{BUSY}}$ = L, data may not be valid, see two and too timing.
- 4. $'H' = V_{IH}$, $'L' = V_{IL}$, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Truth Table II. Interrupt Flag^(1,4)

Left Port							Right Por	rt		
R/₩L	CEL	ŌĒL	A10L-A0L	ÏÑT∟	R/W̄R	CER	OE R	A10R-A0R	Ī NT R	Function
L	L	Х	7FF	Х	Х	Х	Х	X	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	7FF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FE	Х	Set Left INTL Flag
Х	L	L	7FE	H ⁽²⁾	X	Х	Х	X	Х	Reset Left INTL Flag

NOTES:

2654 tbl 14

- 1. Assumes $\overline{BUSY}L = \overline{BUSY}R = VIH$
- 2. If $BUSYL = V_{IL}$, then No Change.
- 3. If BUSYR = VIL, then No Change.
- 4. 'H' = HIGH,' L' = LOW,' X' = DON'T CARE

Functional Description

The IDT70121/125 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70121/125 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{\text{INT}}$ L) is asserted when the right port writes to memory location 7FE (HEX), where a write is defined as the $\overline{\text{CE}}$ = $R/\overline{\text{W}}$ = VIL per Truth Table II. The left port clears the interrupt by access address location 7FE access when $\overline{\text{CE}}$ R = $\overline{\text{OE}}$ R = VIL, $R/\overline{\text{W}}$ is a "don't care". Likewise, the right port interrupt flag (INTR) is asserted when the left port writes to memory location 7FF (HEX) and to clear the interrupt flag (INTR), the right port must access the memory location 7FF. The message (9 bits) at 7FE or 7FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 7FE and 7FF are not used as mail boxes, but as part of the random access memory. Refer to Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a $\overline{\text{BUSY}}$ indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of \overline{BUSY} logic is not desirable, the \overline{BUSY} logic can be disabled by using the IDT70125 (SLAVE). In the IDT70125, the \overline{BUSY} pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the \overline{BUSY} pins HIGH. Once in slave mode the \overline{BUSY} pin operates solely as a write inhibit input pin. If desired, unintended write operations can be prevented to a port by tying the \overline{BUSY} pin for that port LOW.

The BUSY outputs on the IDT70121/125 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70121/125 RAM array in width while using $\overline{\text{BUSY}}$ logic, one master part is used to decide which side of the RAM array will receive a $\overline{\text{BUSY}}$ indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the $\overline{\text{BUSY}}$ signal as a write inhibit signal. Thus on the IDT70121 RAM the $\overline{\text{BUSY}}$ pin is an output of the part, and the BUSY pin is an input of the IDT70125 as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating \overline{BUSY} on one side of the array and another master indicating \overline{BUSY} on one other side of the array. This would inhibit the write operations from one port for part of a word and

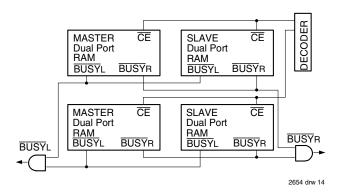


Figure 3. Busy and chip enable routing for both width and depth expansion with 70121 (Master) and 70125 (Slave) RAMs.

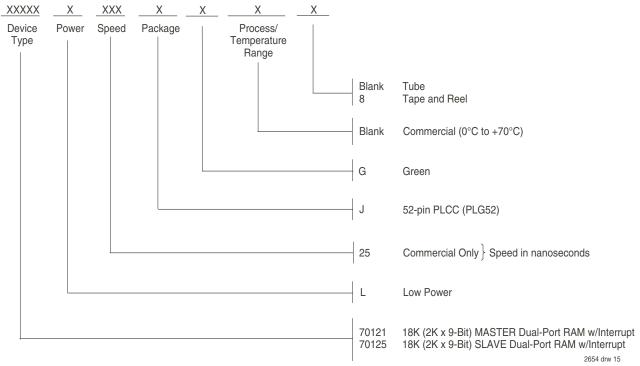
inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a $\overline{\text{BUSY}}$ flag to be output from the master before the actual write pulse can be initiated with either the R/\overline{W} signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.



Commercial Temperature Range

Ordering Information



NOTES:

LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02. Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
25	70121L25JG	PLG52	PLCC	С
	70121L25JG8	PLG52	PLCC	С

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
25	70125L25JG	PLG52	PLCC	С
	70125L25JG8	PLG52	PLCC	С



Commercial Temperature Range

Datasheet Document History

10/10/17:

09/16/19:

Page 6,8,10&12 Page 15

Page 1 & 15

Page 2 Page 15

04/07/00		
01/06/99:		Initiated datasheet document history
		Converted to new format
	D 0 10	Cosmetic and typographical corrections
0./ 10.0 10.0	Pages 2 and 3	Added additional notes to pin configurations
06/03/99:	5 4	Changed drawing format
05/00/04	Page 1	Corrected DSC number
05/28/04:	Page 3	Changed storage temperature parameter from -55 to +125 to -65 to +150
		Clarified TA parameter footnote
	Page 4	DC Electrical parameters—changed test condition wording from "open" to "disabled"
	Page 9	Changed ±500mV to 0mV in notes
	Page 2	Added date revision for pin configuration
		2 Added Industrial temp to column headings for 35ns speed to DC and AC Electrical Characteristics
	Page 4	Removed Industrial temp from 25, 45 & 55ns speeds from DC Electrical Characteristics
	Page 3, 4, 6, 8, 108	&12 Removed Industrial temp footnote from all tables
	Page 10	Corrected error in AC BUSY timing tables changing 71V33 to 70121 and changing 71V43 to 70125
	Page 15	Added Industrial temp offering to 35ns ordering information
	Page 1 & 15	Replaced old тм logo with new тм logo
	Page 6	Footnote reference 5 removed from AC Electrical Characteristics READ table
	Page 1	Changed wording of footnote 1 from "INT is to tem-pole output" to "INT is non-tr-stated push-pull output"
	Page 5	Updated AC Test Conditions Input Rise/Fall Times from 5ns to 3ns
04/05/06:	Page 1	Added green availability to features
	Page 15	Added green indicator to ordering information
10/21/08:	Page 15	Removed "IDT" from orderable part number
08/05/14:	Page 1	Added green availability to Features
	Page 15	Added green indicator to Ordering Information
	Page 2 &15	The package code for the J52-1 changed to J52 to match standard package code
	Page 15	Added Tape and Reel to Ordering Information
08/27/14:	Page 1	Removed 45ns commercial speed grade from Features High-speed access information
	Page 1-16	Removed 45ns commercial speed grade throughout the datasheet to correct a discrepancy in
	J	IDT's product catalog
	Page 4	Specifically including the DC Chars table
	D (040040	

Specifically including the AC Chars tables

Last time buy expires June 15, 2018

Added Orderable Part Information table

Product Discontinuation Notice - PDN# SP-17-02

Removed 45ns commercial speed grade from the Ordering Information

Deleted obsolete Commercial speed grades 35/55ns and Industrial speed grade 35ns

Rotated PLG52 PLCC pin configuration to accurately reflect pin 1 orientation

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(Rev.1.0 Mar 2020)

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CY62157G30-45ZSXI 71V016SA12YG RMLV0416EGBG-4S2#AC0 CY62126EV18LL-70BVXI